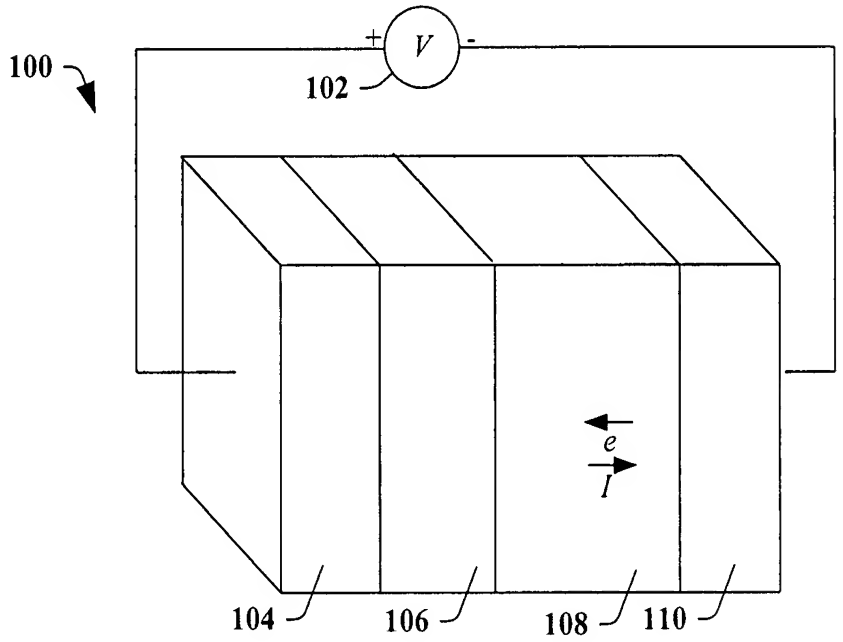

100
+
V
-
102
e
I
104
106
108
110

Fig. 1

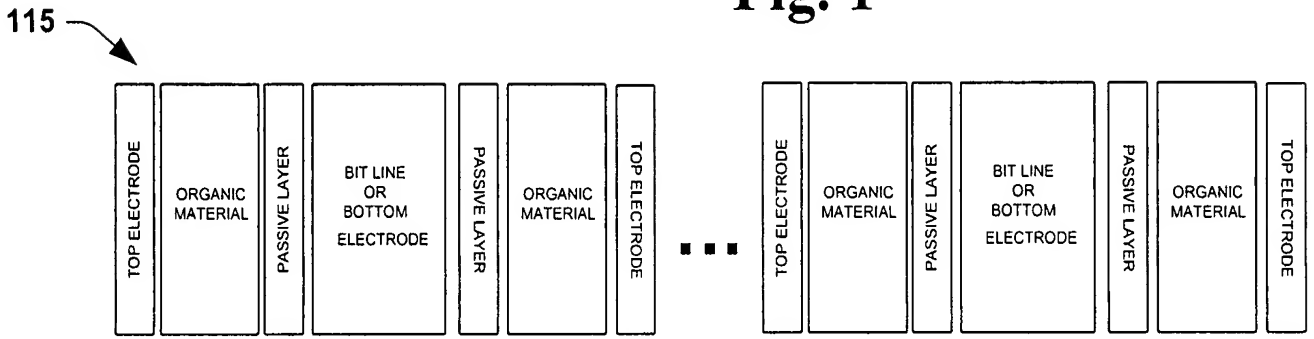

115
TOP ELECTRODE
ORGANIC MATERIAL
PASSIVE LAYER
BIT LINE OR BOTTOM ELECTRODE
PASSIVE LAYER
ORGANIC MATERIAL
TOP ELECTRODE
TOP ELECTRODE
ORGANIC MATERIAL
PASSIVE LAYER
BIT LINE OR BOTTOM ELECTRODE
PASSIVE LAYER
ORGANIC MATERIAL
TOP ELECTRODE

Fig. 1(a)

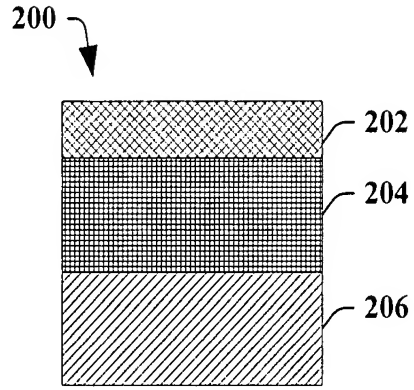


Fig. 2

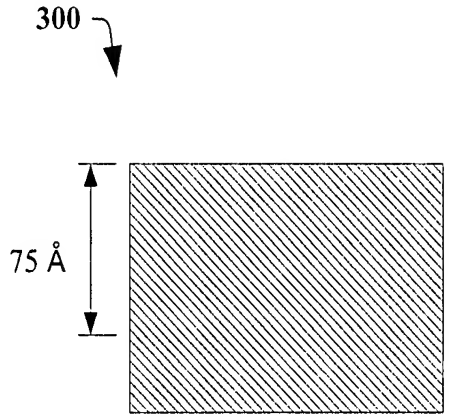


Fig. 3

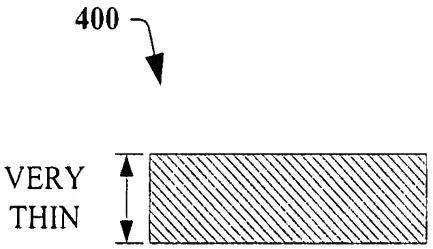


Fig. 4

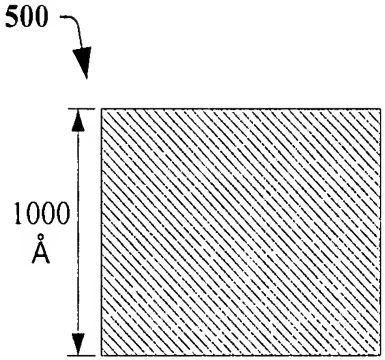


Fig. 5

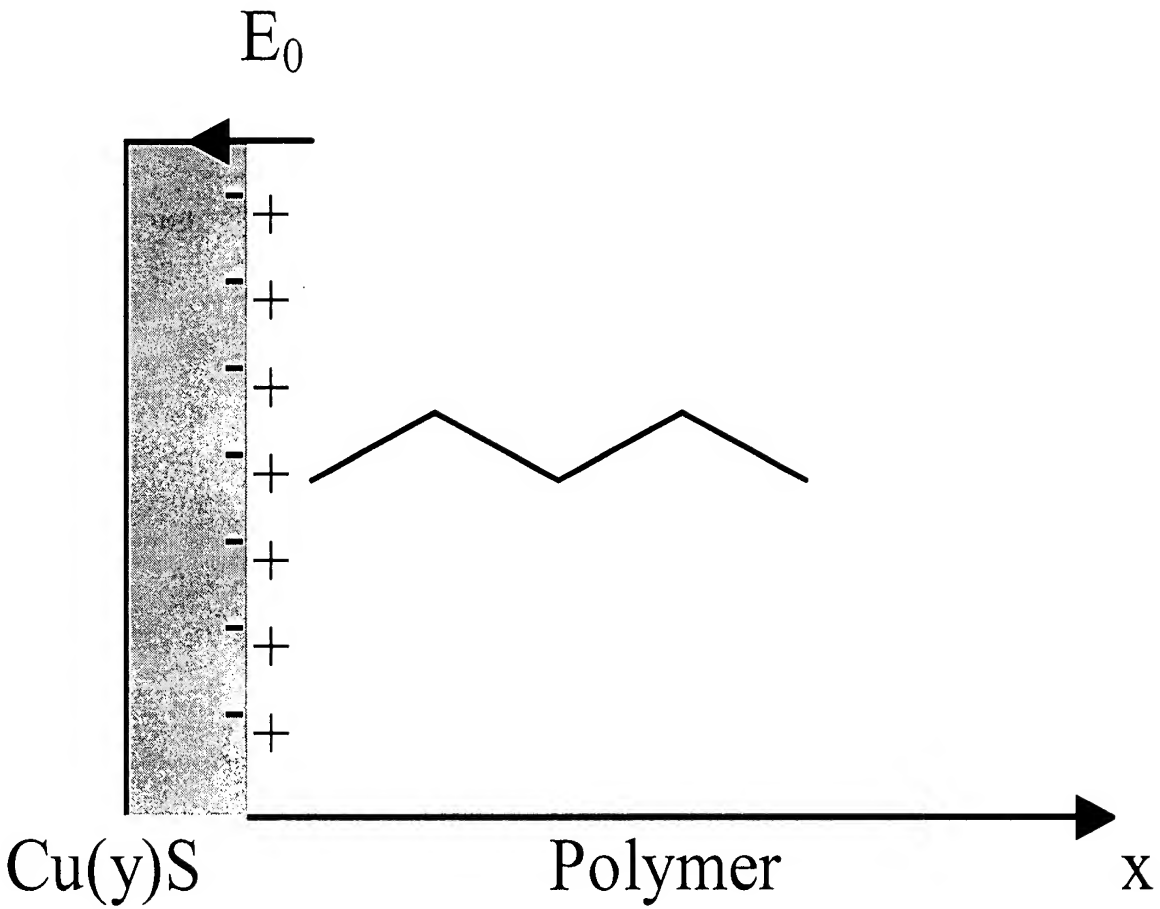


Fig. 6

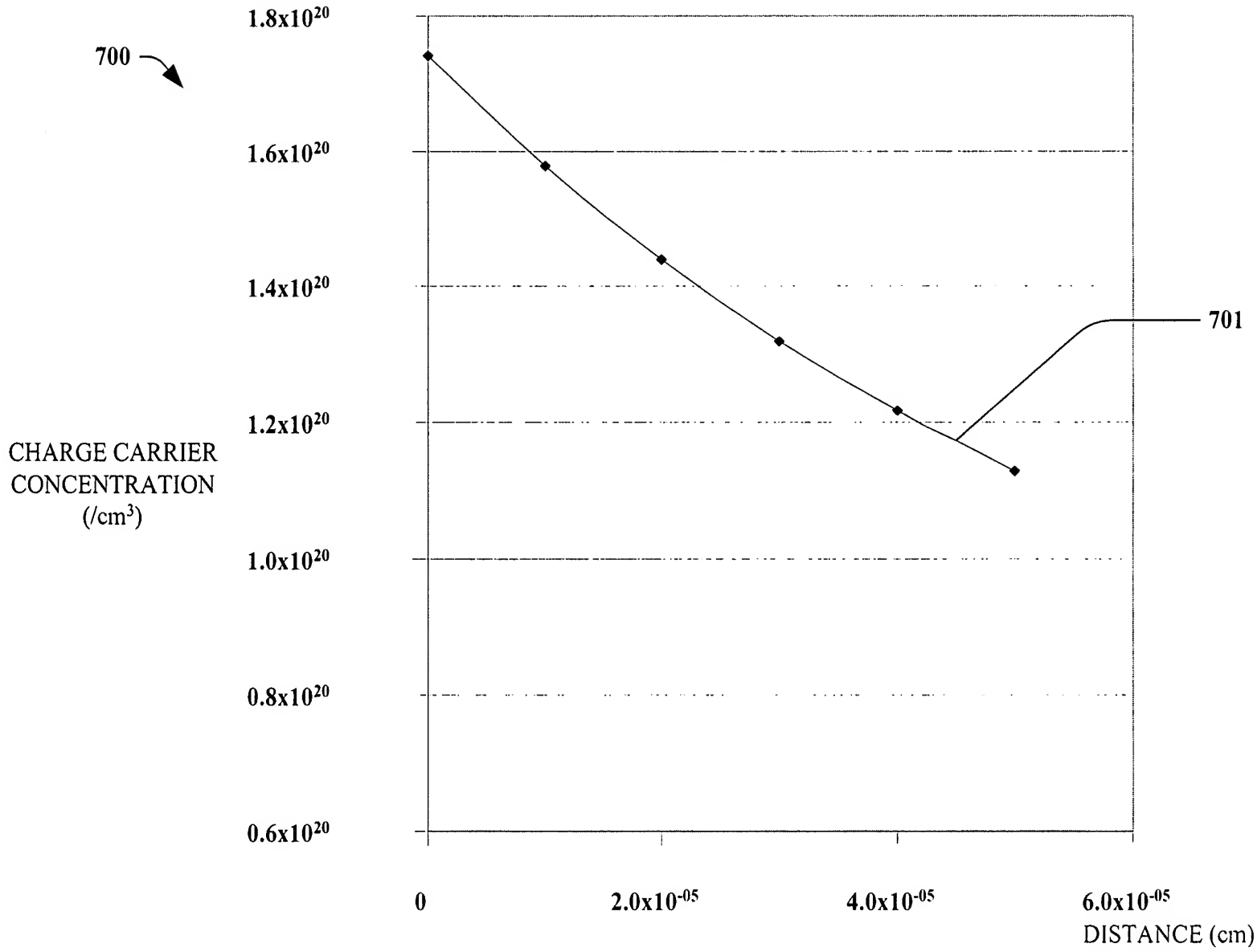

700
1.8x10^20
1.6x10^20
1.4x10^20
1.2x10^20
1.0x10^20
0.8x10^20
0.6x10^20
CHARGE CARRIER CONCENTRATION (/cm^3)
701
0
2.0x10^-05
4.0x10^-05
6.0x10^-05
DISTANCE (cm)

Fig. 7

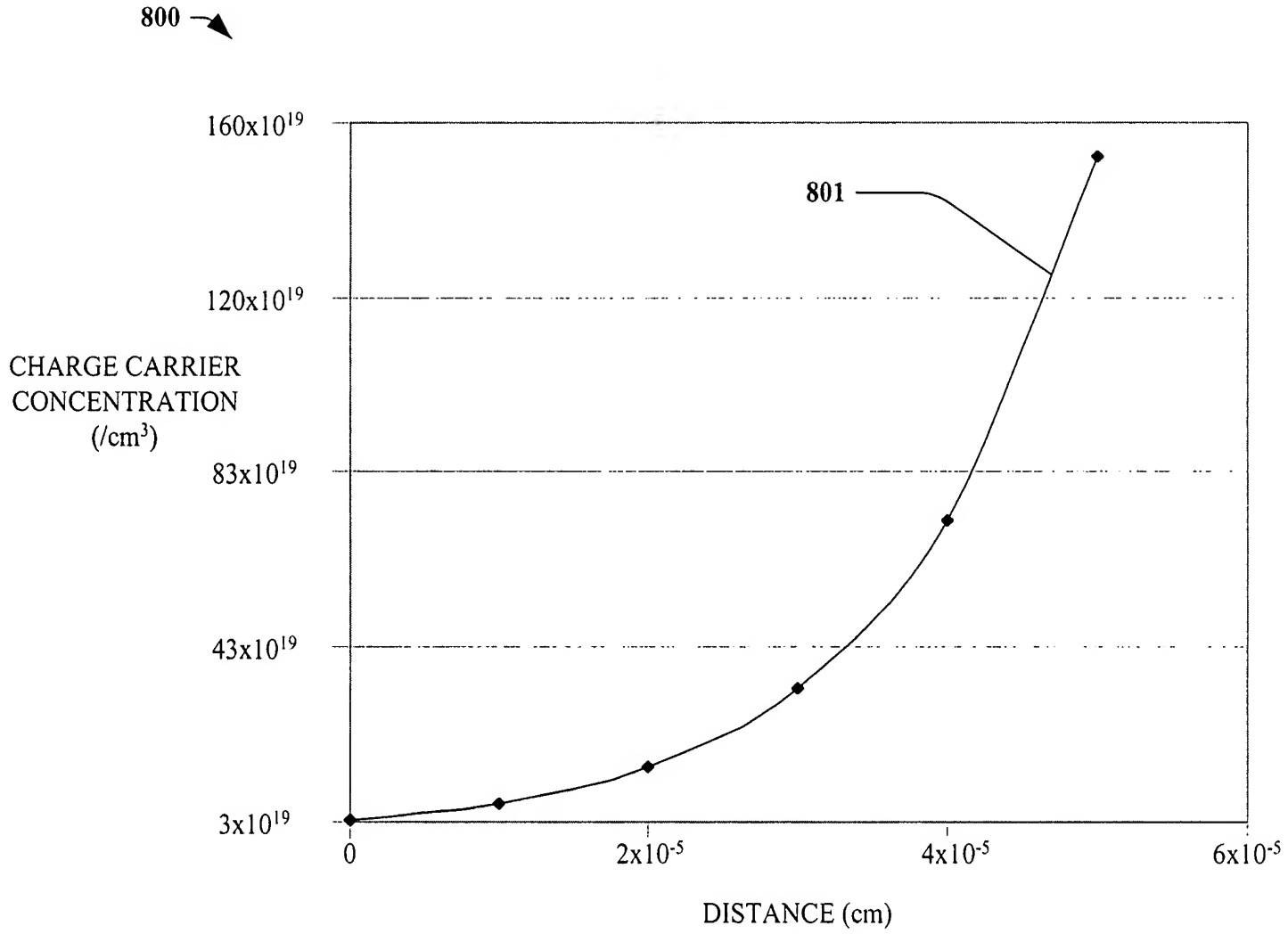

800
160x10^19
120x10^19
83x10^19
43x10^19
3x10^19
CHARGE CARRIER CONCENTRATION (/cm^3)
801
0
2x10^-5
4x10^-5
6x10^-5
DISTANCE (cm)

Fig. 8

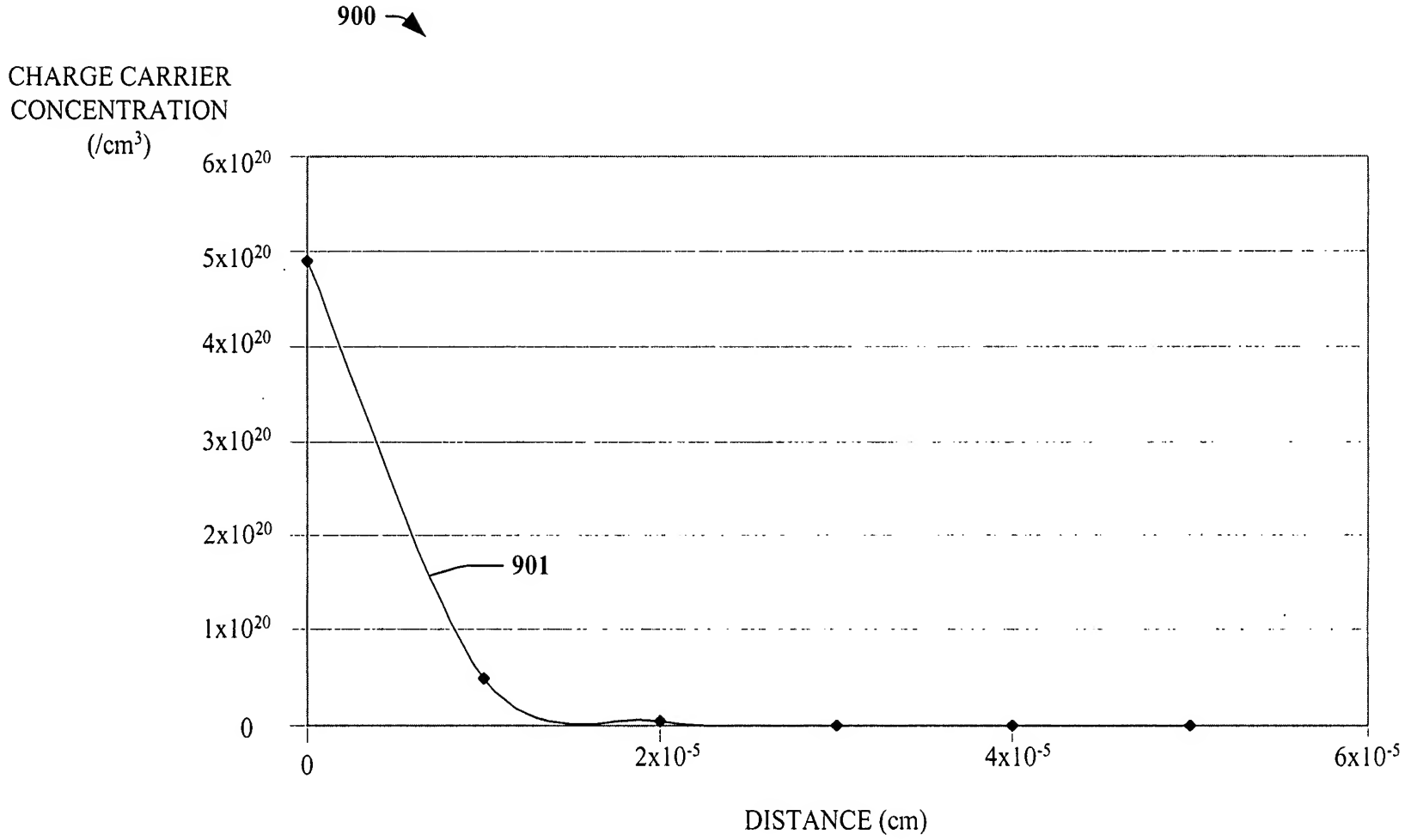

900
CHARGE CARRIER CONCENTRATION (/cm3)
6x10^20
5x10^20
4x10^20
3x10^20
2x10^20
1x10^20
0
901
0
2x10^-5
4x10^-5
6x10^-5
DISTANCE (cm)

Fig. 9

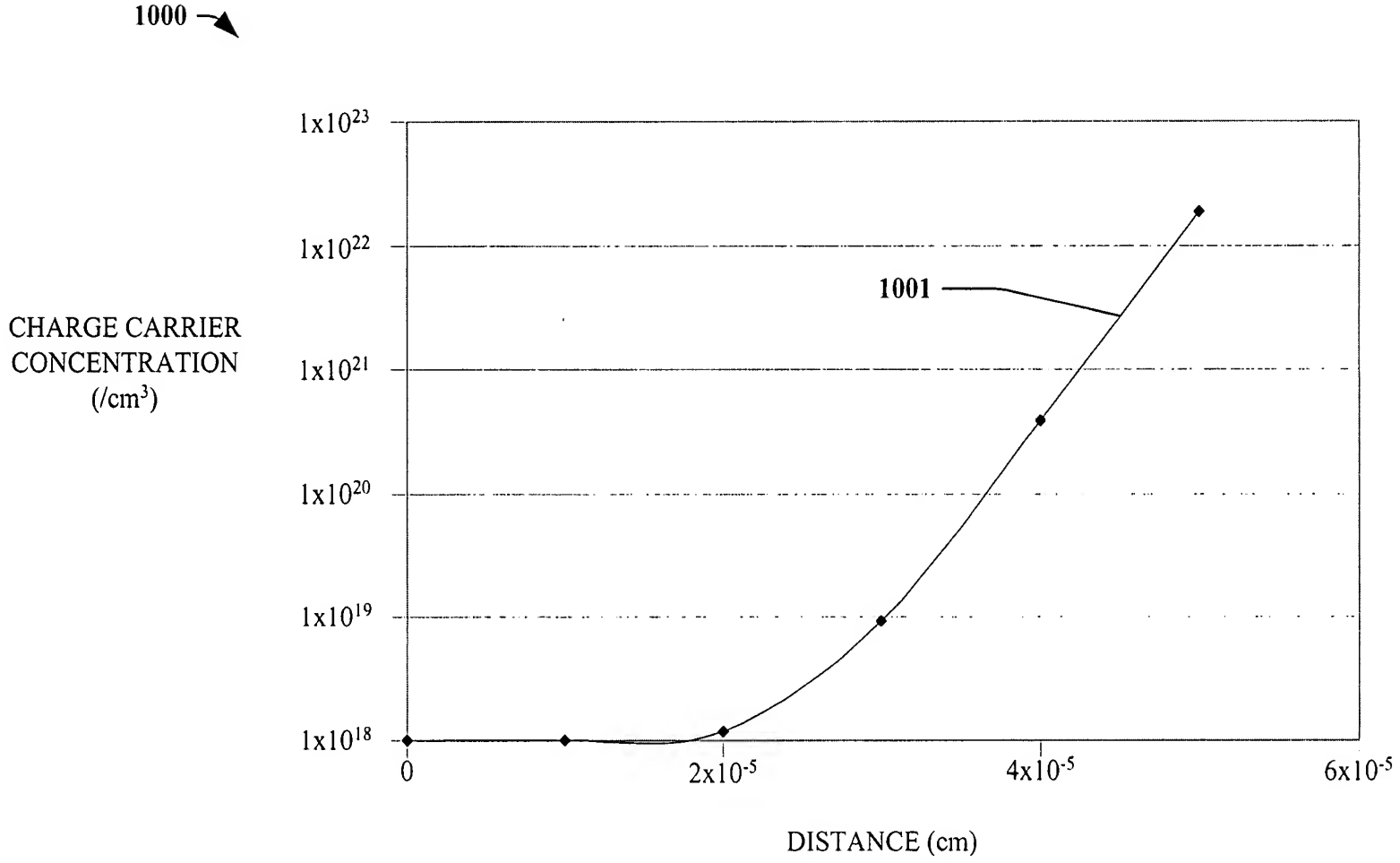

1000
1x10^23
1x10^22
1x10^21
1x10^20
1x10^19
1x10^18
CHARGE CARRIER CONCENTRATION (/cm^3)
1001
0
2x10^-5
4x10^-5
6x10^-5
DISTANCE (cm)

Fig. 10

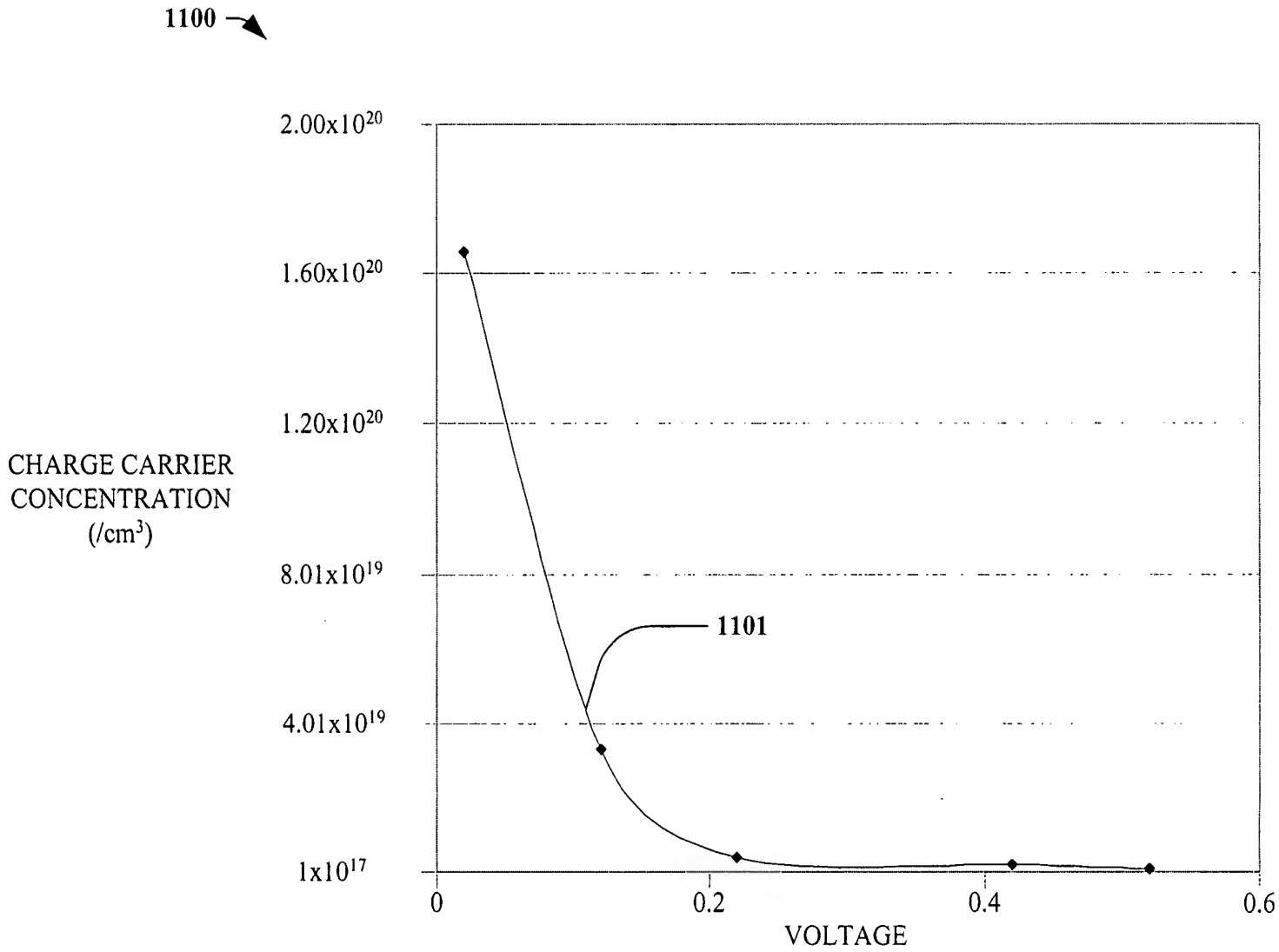

1100
2.00x10^20
1.60x10^20
1.20x10^20
8.01x10^19
4.01x10^19
1x10^17
CHARGE CARRIER CONCENTRATION (/cm^3)
1101
0
0.2
0.4
0.6
VOLTAGE

Fig. 11

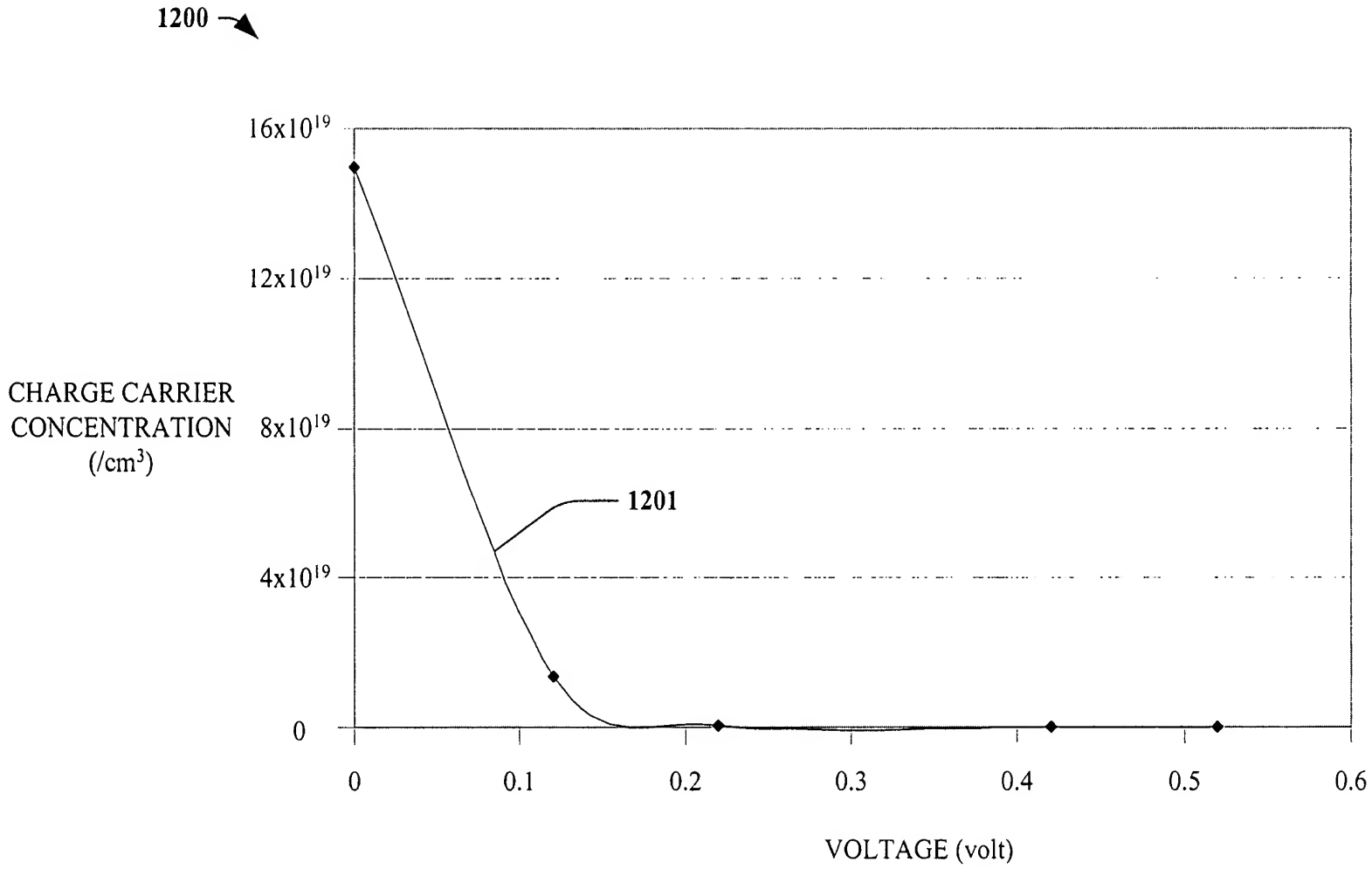

1200
16x10^19
12x10^19
8x10^19
4x10^19
0
CHARGE CARRIER CONCENTRATION (/cm^3)
1201
0
0.1
0.2
0.3
0.4
0.5
0.6
VOLTAGE (volt)

Fig. 12

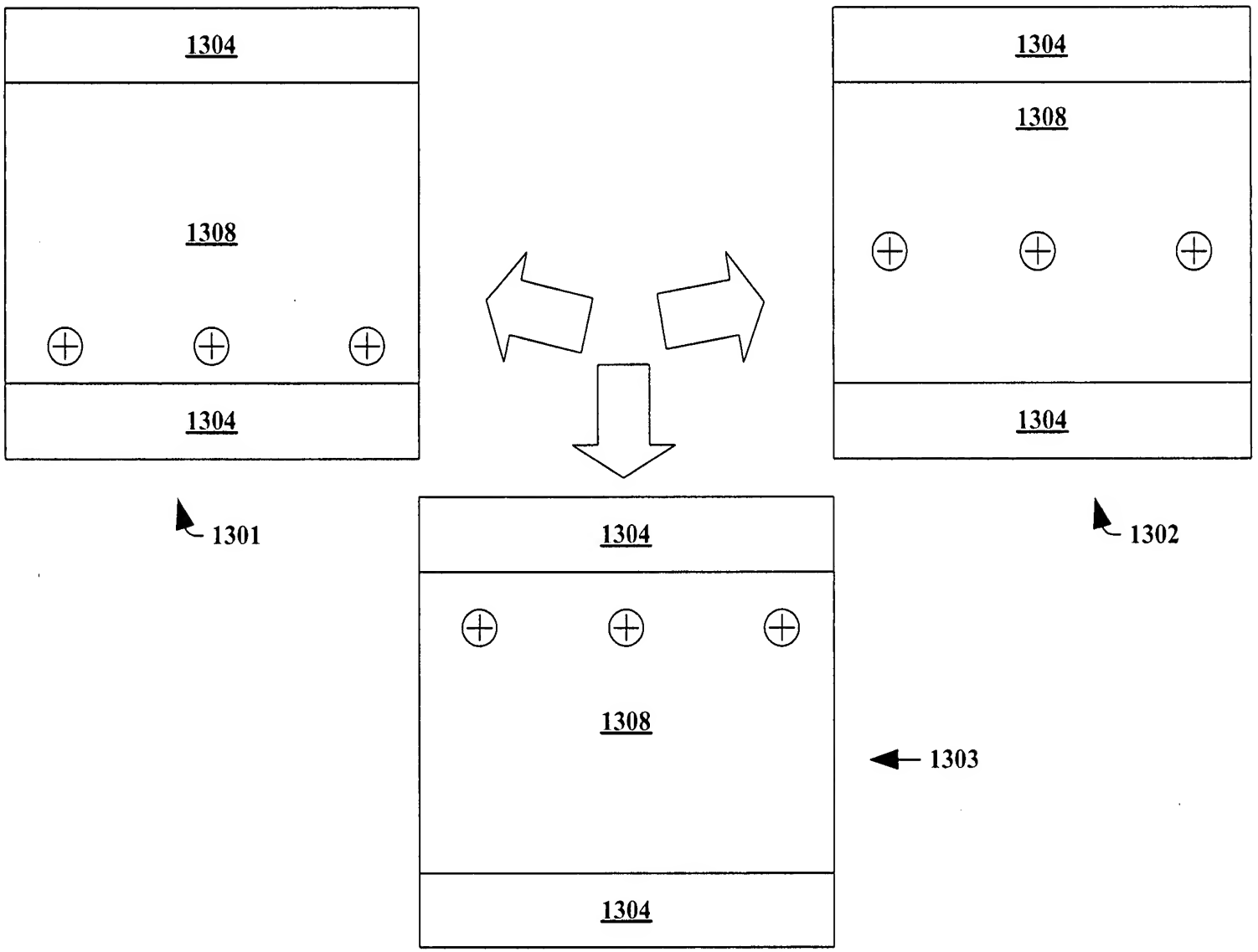


Fig. 13

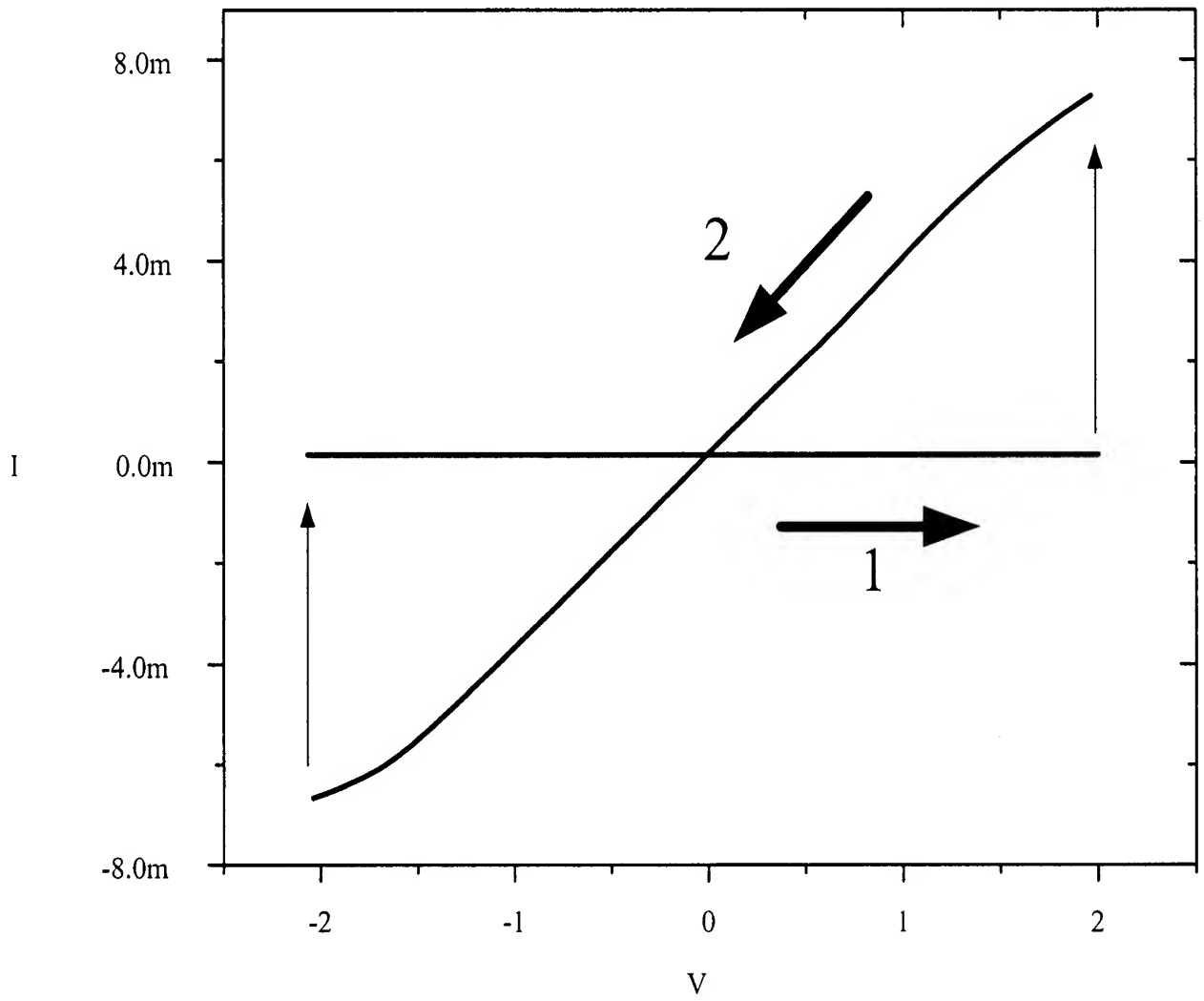


Fig. 14

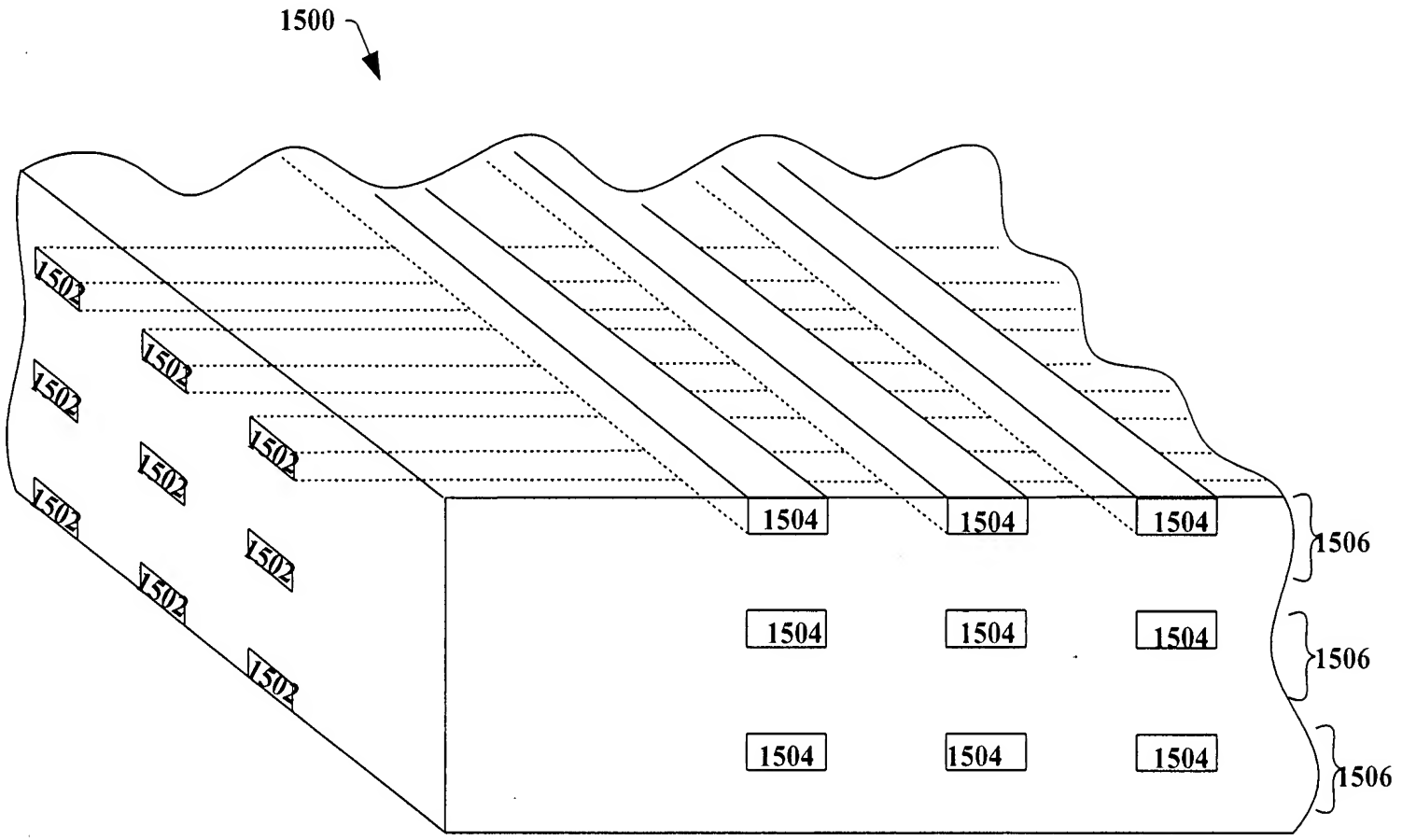


Fig. 15

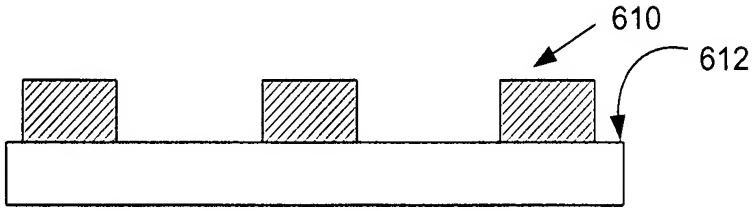


Fig. 16(a)

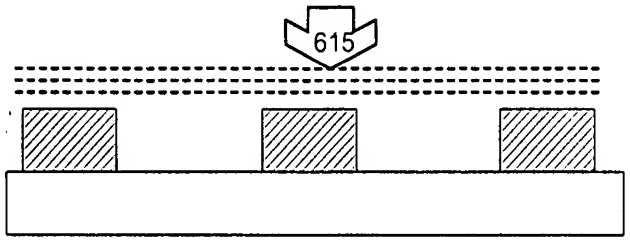


Fig. 16(b)

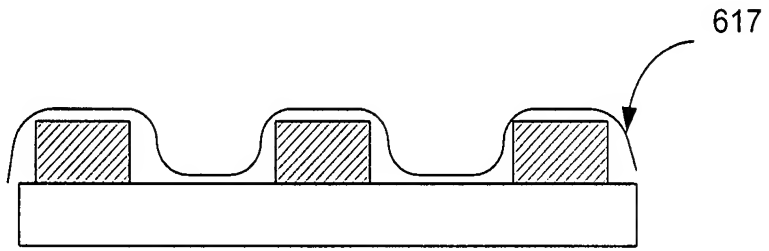


Fig. 16(c)

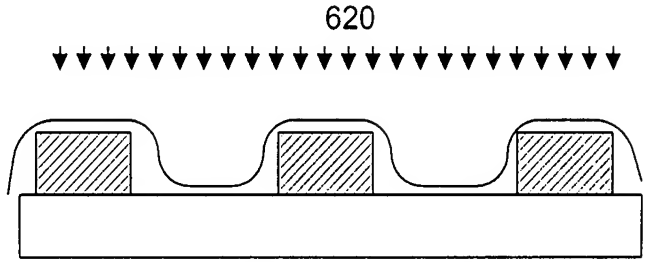


Fig. 16(d)

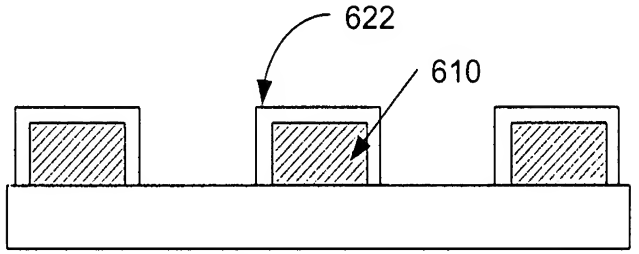


Fig. 16(e)

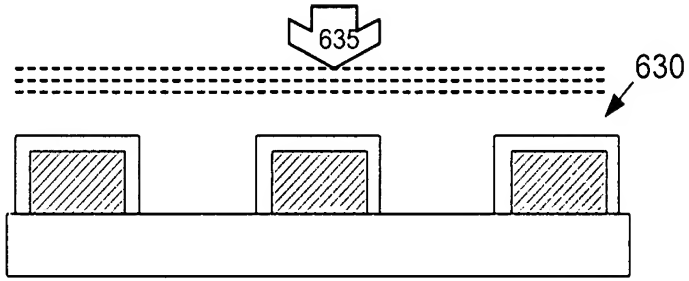


Fig. 16(f)

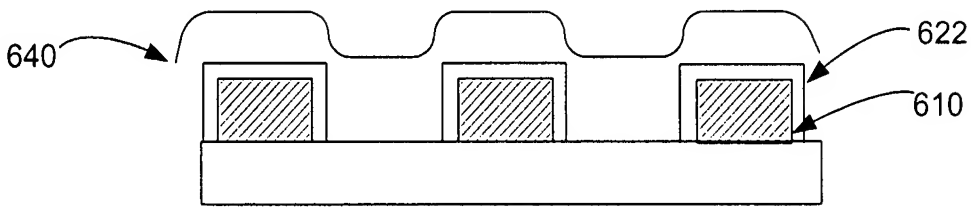


Fig. 16(g)

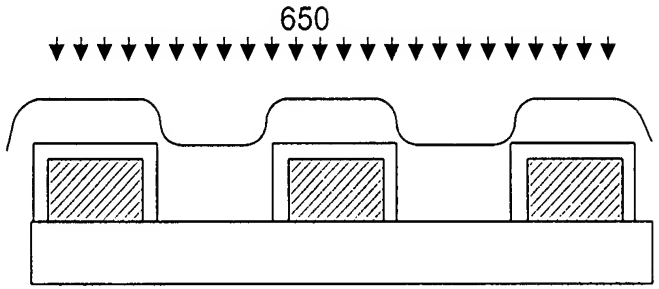


Fig. 16(h)

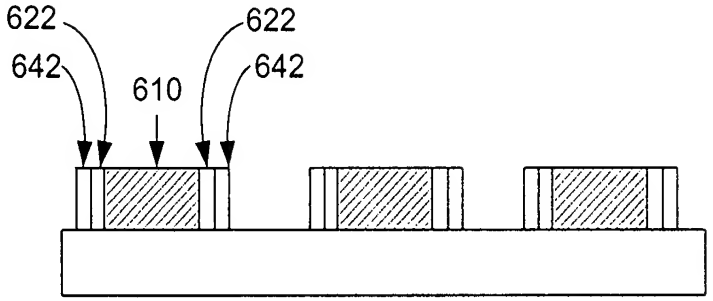
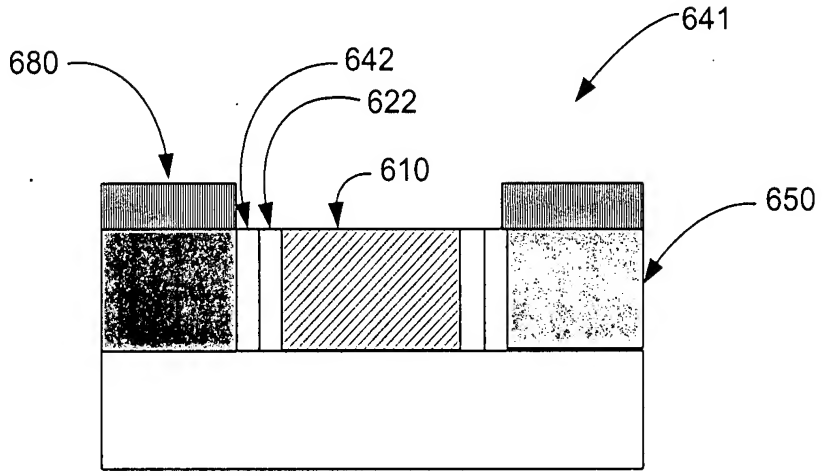


Fig. 16(i)



SIDE VIEW

TOP VIEW

Fig. 16(j)

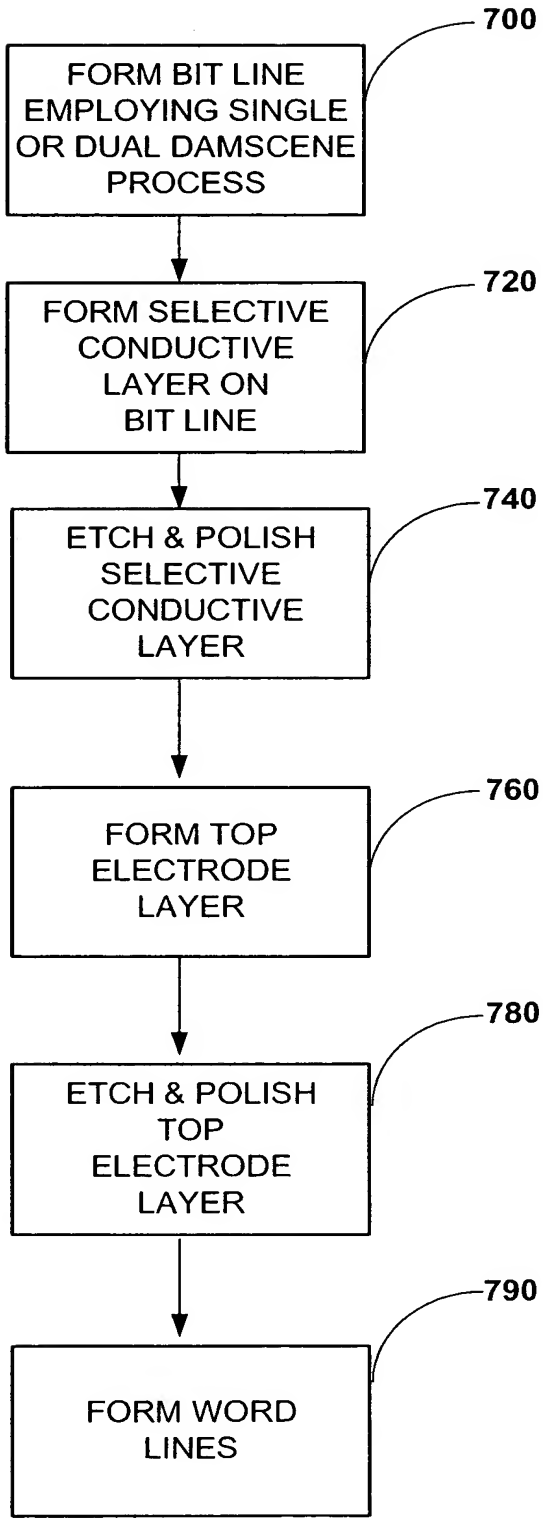

700
FORM BIT LINE EMPLOYING SINGLE OR DUAL DAMSCENE PROCESS
720
FORM SELECTIVE CONDUCTIVE LAYER ON BIT LINE
740
ETCH & POLISH SELECTIVE CONDUCTIVE LAYER
760
FORM TOP ELECTRODE LAYER
780
ETCH & POLISH TOP ELECTRODE LAYER
790
FORM WORD LINES

Fig. 17

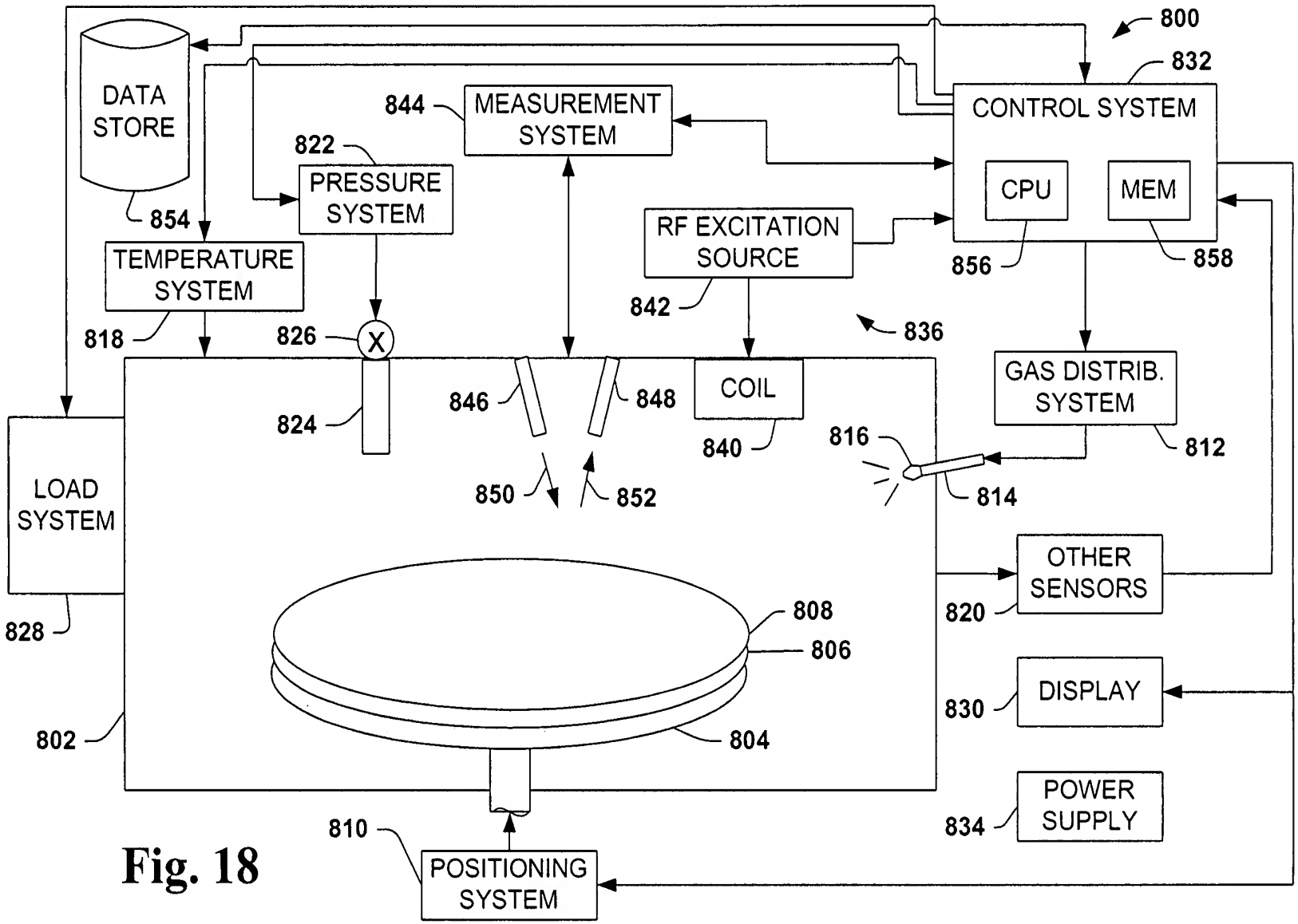
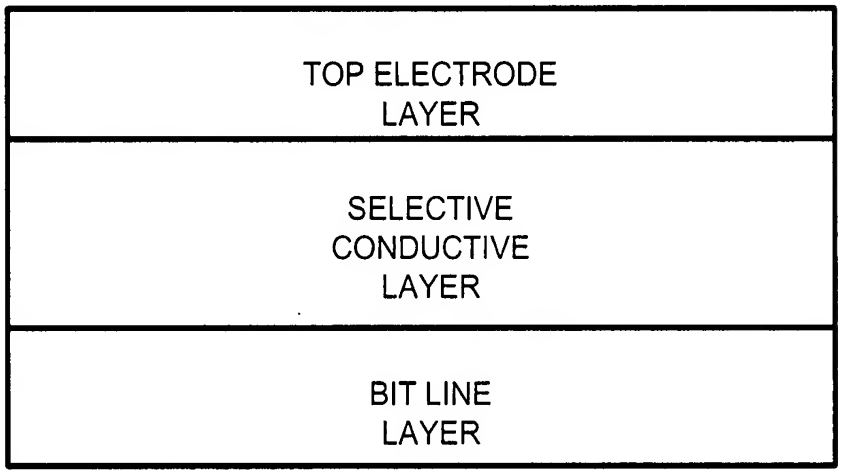

800
832
DATA STORE
854
844
MEASUREMENT SYSTEM
CONTROL SYSTEM
822
PRESSURE SYSTEM
CPU
MEM
RF EXCITATION SOURCE
856
858
TEMPERATURE SYSTEM
842
818
826
836
GAS DISTRIB. SYSTEM
846
848
COIL
824
840
816
812
LOAD SYSTEM
850
852
814
OTHER SENSORS
808
828
820
806
DISPLAY
830
802
804
POWER SUPPLY
834
810
POSITIONING SYSTEM

Fig. 18



(PRIOR ART)

Fig. 19